

MOSFETs Silicon N-Channel MOS (U-MOSVI-H)

TK60P03M1

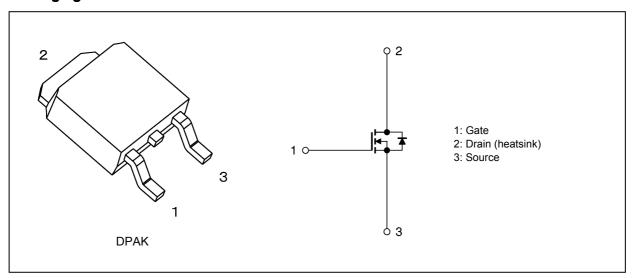
1. Applications

- · DC-DC Converters
- · Desktop Computers

2. Features

- (1) High-speed switching
- (2) Low gate charge: $Q_{SW} = 13 \text{ nC (typ.)}$
- (3) Low drain-source on-resistance: $R_{DS(ON)} = 4.6 \text{ m}\Omega$ (typ.) ($V_{GS} = 10 \text{ V}$)
- (4) Low leakage current: $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 30 \text{ V)}$
- (5) Enhancement mode: $V_{th} = 1.3$ to 2.3 V ($V_{DS} = 10$ V, $I_D = 0.5$ mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (T_a = 25°C unless otherwise specified)

| Chara | Symbol | Rating | Unit | | |
|-------------------------------|---------------------------|----------|------------------|------------|----|
| Drain-source voltage | | | V _{DSS} | 30 | V |
| Drain-gate voltage | (R _{GS} = 20 kΩ) | | V_{DGR} | 30 | |
| Gate-source voltage | | | V _{GSS} | ±20 | |
| Drain current (DC) | | (Note 1) | I _D | 60 | А |
| Drain current (pulsed) | | (Note 1) | I _{DP} | 120 | |
| Power dissipation | (T _c = 25°C) | | P _D | 63 | W |
| Single-pulse avalanche energy | | (Note 2) | E _{AS} | 94 | mJ |
| Avalanche current | | | I _{AR} | 60 | Α |
| Channel temperature | | | T _{ch} | 150 | °C |
| Storage temperature | | | T _{stg} | -55 to 150 | |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).



5. Thermal Characteristics

| Characteristics | Symbol | Max | Unit |
|---------------------------------------|-----------------------|------|------|
| Channel-to-case thermal resistance | R _{th(ch-c)} | 1.98 | °C/W |
| Channel-to-ambient thermal resistance | R _{th(ch-a)} | 125 | |

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_{DD} = 24 V, T_{ch} = 25°C (initial), L = 0.02 mH, R_G = 1.2 Ω , I_{AR} = 60 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25°C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|----------------------|---|-----|------|------|------|
| Gate leakage current | I _{GSS} | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$ | _ | _ | ±0.1 | μА |
| Drain cut-off current | I _{DSS} | V _{DS} = 30 V, V _{GS} = 0 V | _ | _ | 10 | |
| Drain-source breakdown voltage | V _{(BR)DSS} | I _D = 10 mA, V _{GS} = 0 V | 30 | | | V |
| | V _{(BR)DSX} | I _D = 10 mA, V _{GS} = -20 V | 15 | | | |
| Gate threshold voltage | V_{th} | V _{DS} = 10 V, I _D = 0.5 mA | 1.3 | _ | 2.3 | |
| Drain-source on-resistance | R _{DS(ON)} | V _{GS} = 4.5 V, I _D = 30 A | | 5.7 | 7.8 | mΩ |
| | | V _{GS} = 10 V, I _D = 30 A | _ | 4.6 | 6.4 | |

6.2. Dynamic Characteristics (T_a = 25°C unless otherwise specified)

| Characteristics | Symbol | mbol Test Condition | | Тур. | Max | Unit |
|--------------------------------|------------------|--|---|------|-----|------|
| Input capacitance | C _{iss} | V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz | - | 2700 | _ | pF |
| Reverse transfer capacitance | C _{rss} | | _ | 170 | _ | |
| Output capacitance | C _{oss} | | 1 | 520 | | |
| Gate resistance | r _g | V _{DS} = 10 V, V _{GS} = 0 V, f = 5 MHz | _ | 0.7 | 1.1 | Ω |
| Switching time (rise time) | t _r | See Figure 6.2.1. | 1 | 4.3 | | ns |
| Switching time (turn-on time) | t _{on} | | | 15 | | |
| Switching time (fall time) | t _f | | _ | 11 | | |
| Switching time (turn-off time) | t _{off} | | _ | 32 | | |

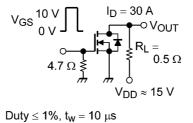


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25°C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|-------------------------------------|------------------|--|-----|------|-----|------|
| Total gate charge (gate-source plus | Q_g | $V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 60 \text{ A}$ | _ | 40 | 1 | nC |
| gate-drain) | | $V_{DD} \approx 24 \text{ V}, V_{GS} = 5 \text{ V}, I_{D} = 60 \text{ A}$ | | 21 | | |
| Gate-source charge 1 | Q _{gs1} | $V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 60 \text{ A}$ | | 11 | | |
| Gate-drain charge | Q_{gd} | | | 7.2 | | |
| Gate switch charge | Q_SW | | _ | 13 | _ | |

6.4. Source-Drain Characteristics (T_a = 25°C unless otherwise specified)

| Characteristics | | Symbol | Test Condition | Min | Тур. | Max | Unit |
|-----------------------------------|---------|------------------|---|-----|------|------|------|
| Reverse drain current (pulsed) (N | Note 3) | I _{DRP} | _ | _ | _ | 120 | Α |
| Diode forward voltage | | V_{DSF} | I _{DR} = 60 A, V _{GS} = 0 V | _ | _ | -1.2 | V |

Note 3: Ensure that the channel temperature does not exceed 150°C.



7. Marking

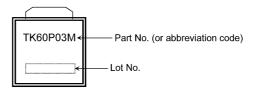


Fig. 7.1 Marking

8. Characteristics Curves (Note)

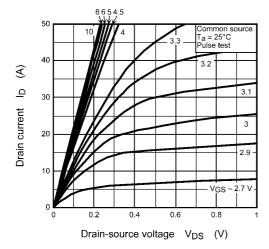


Fig. 8.1 $I_D - V_{DS}$

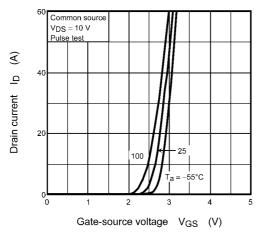


Fig. 8.3 $I_D - V_{GS}$

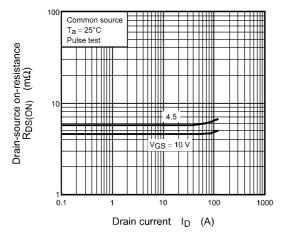


Fig. 8.5 R_{DS(ON)} - I_D

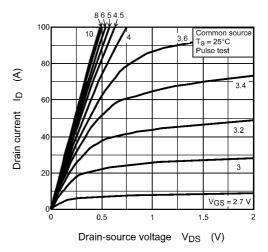


Fig. 8.2 I_D - V_{DS}

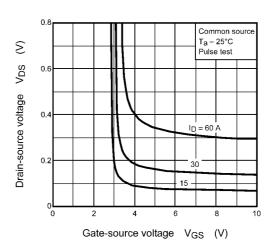


Fig. 8.4 V_{DS} - V_{GS}

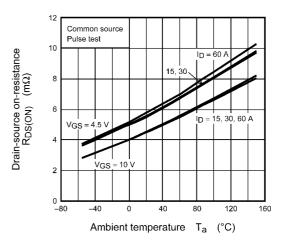


Fig. 8.6 R_{DS(ON)} - T_a

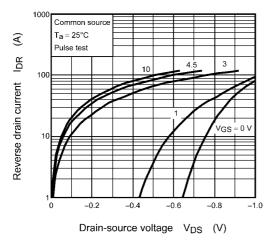


Fig. 8.7 I_{DR} - V_{DS}

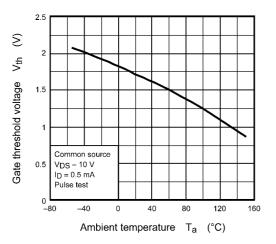


Fig. 8.9 Vth - Ta

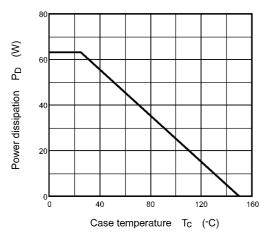


Fig. 8.11 P_D - T_c (Guaranteed Maximum)

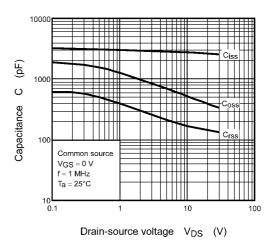


Fig. 8.8 Capacitance - V_{DS}

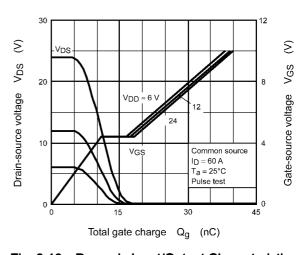


Fig. 8.10 Dynamic Input/Output Characteristics

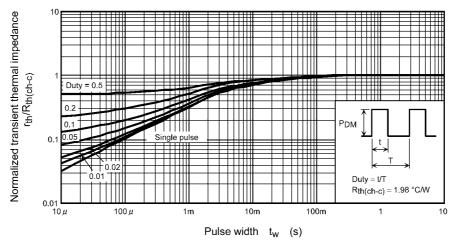


Fig. 8.12 $r_{th}/R_{th(ch-c)} - t_w$ (Guaranteed Maximum)

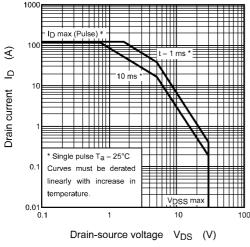


Fig. 8.13 Safe Operating Area (Guaranteed Maximum)

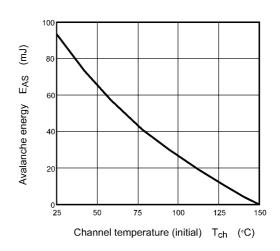


Fig. 8.14 E_{AS} - T_{ch} (Guaranteed Maximum)

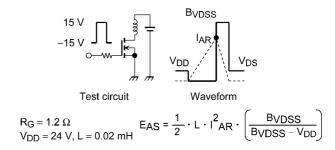


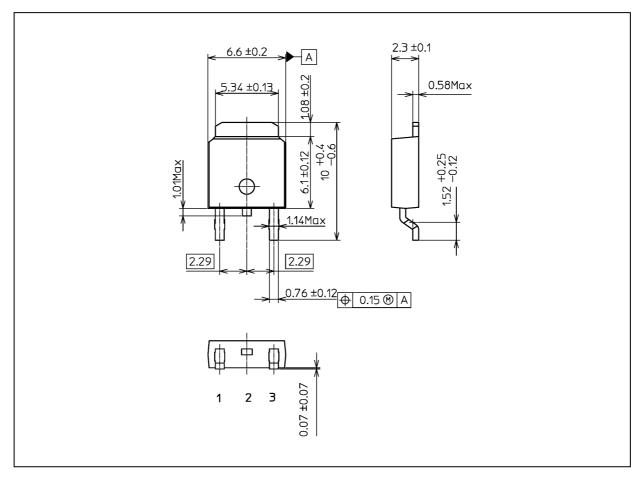
Fig. 8.15 Test Circuit/Waveform

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 0.36 g (typ.)

| Package Name(s) |
|-----------------|
| TOSHIBA: 2-7K1S |
| Nickname: DPAK |

Rev.2.0



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